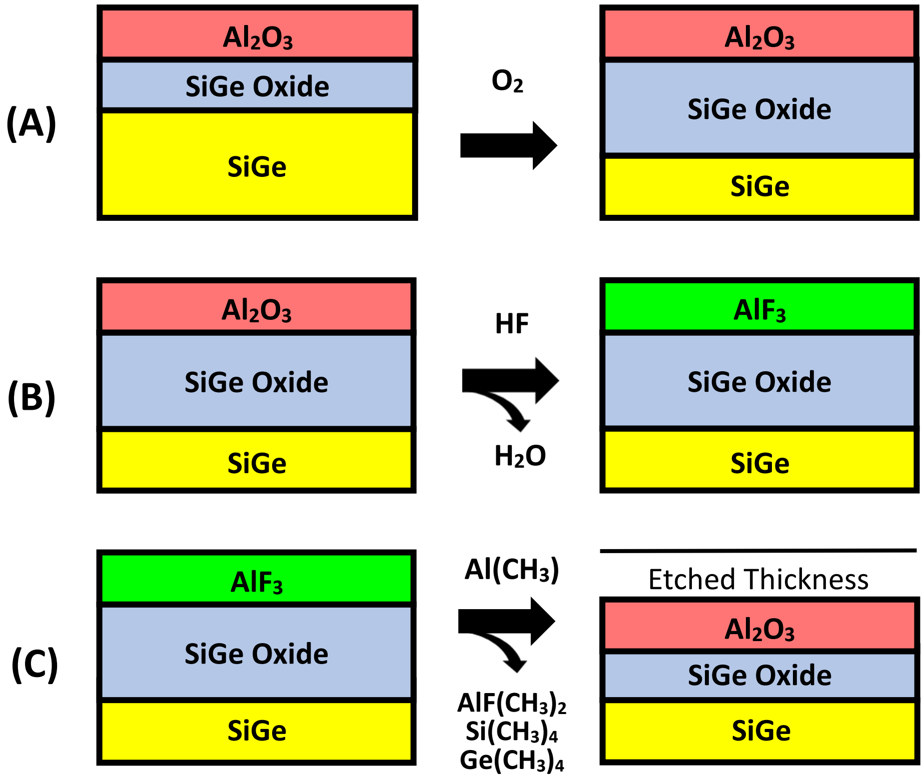

Figure 1. Schematic for thermal SiGe ALE based on (A) oxidation; (B) fluorination; and (C) ligand-exchange and conversion.

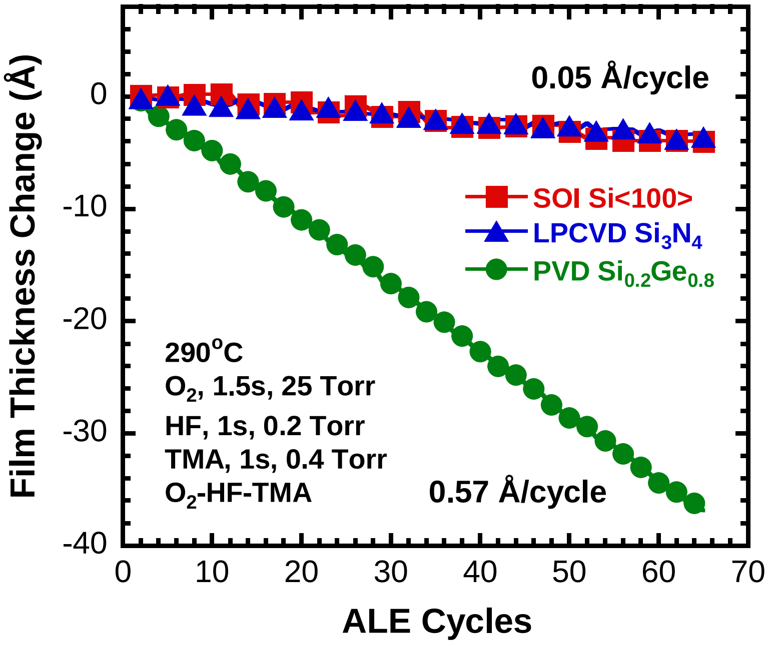

Figure 2. Thermal ALE of Si<100>, Si_3N_4, $Si_{0.2}Ge_{0.8}$ at 290°C using sequential exposures of O_2, HF and TMA